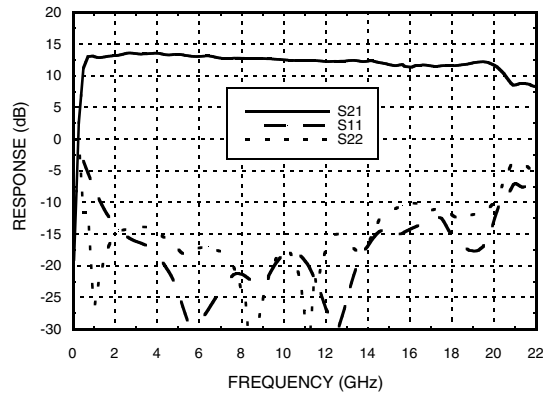
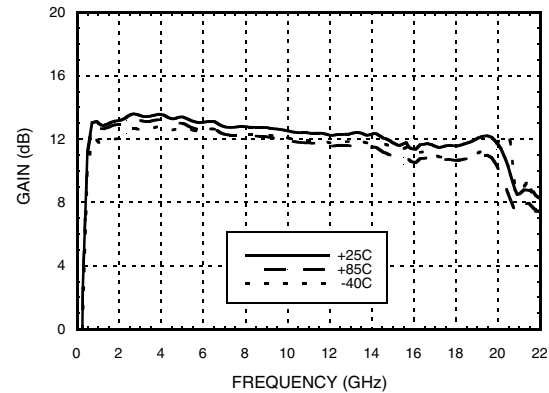


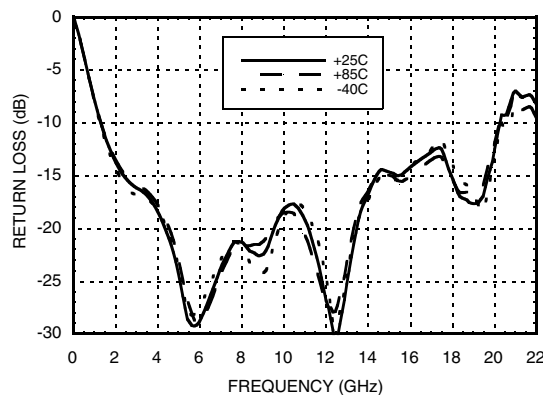
Gain & Return Loss



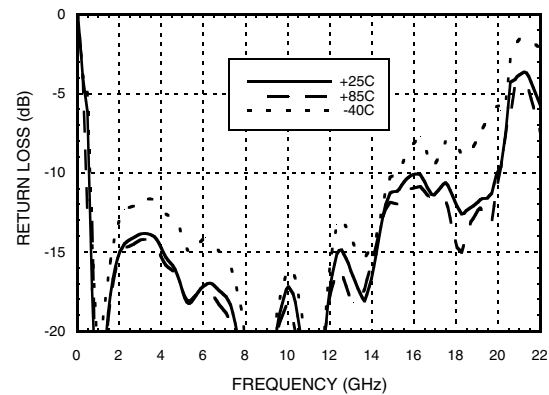
Gain vs. Temperature



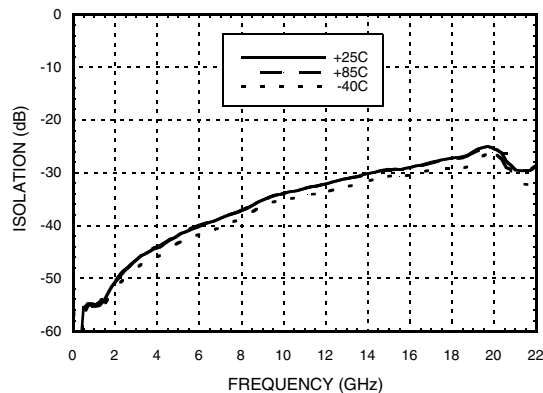
Input Return Loss vs. Temperature



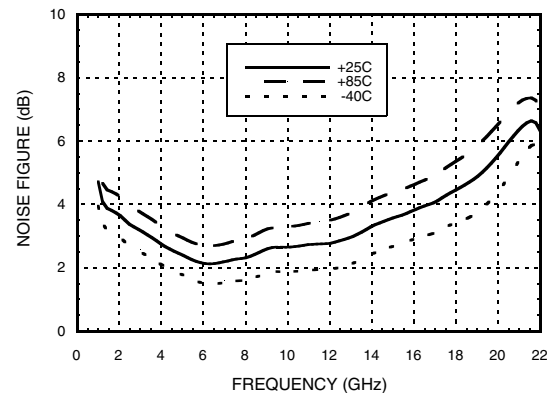
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature

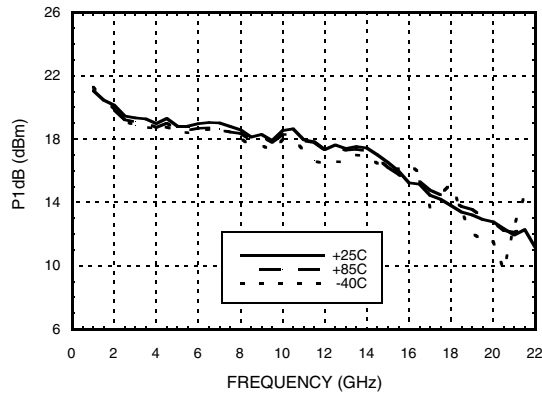


**GaAs pHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**

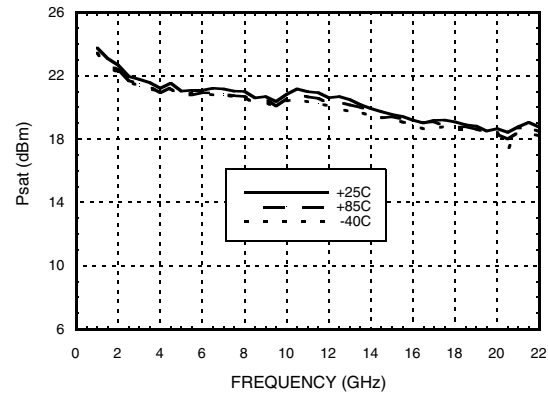
7

AMPLIFIERS - LOW NOISE - SMT

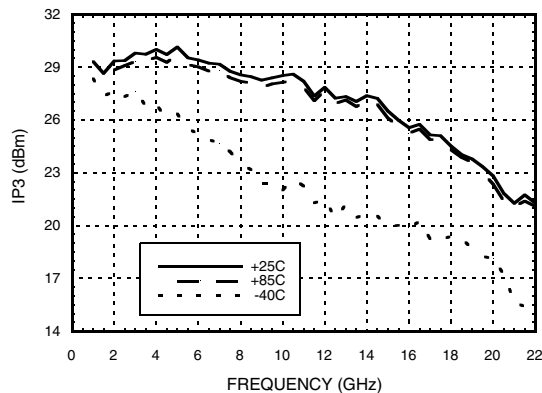
P1dB vs. Temperature



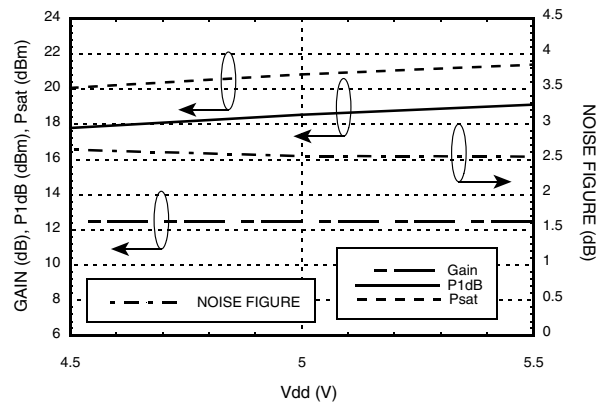
Psat vs. Temperature



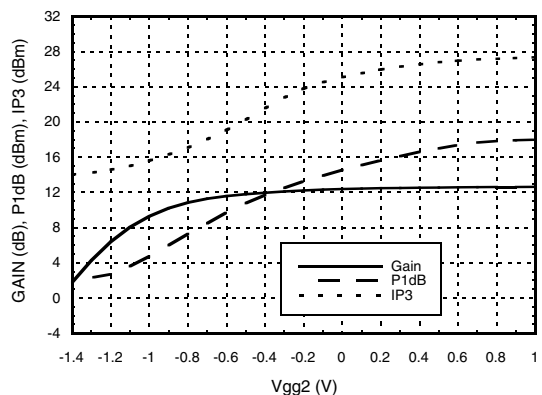
Output IP3 vs. Temperature



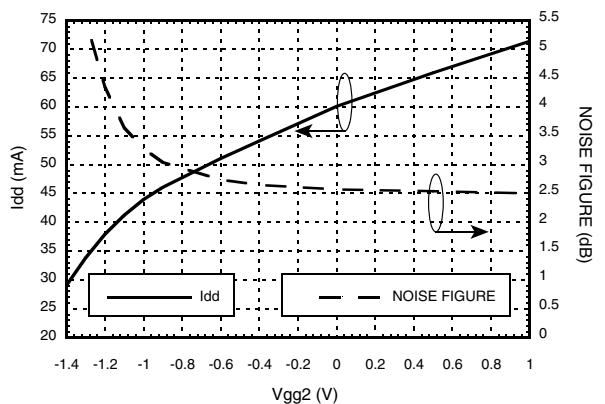
**Gain, Power & Noise Figure
vs. Supply Voltage @ 10 GHz, Fixed Vgg1**

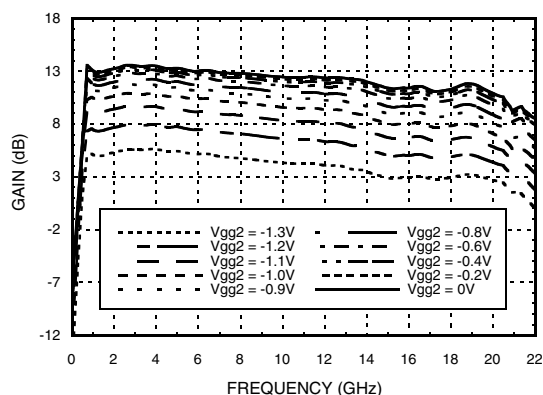


**Gain, P1dB & Output IP3
vs. Control Voltage @ 10 GHz**



**Noise Figure & Supply Current
vs. Control Voltage @ 10 GHz**



Gain @ Several Control Voltages (V_{gg2})


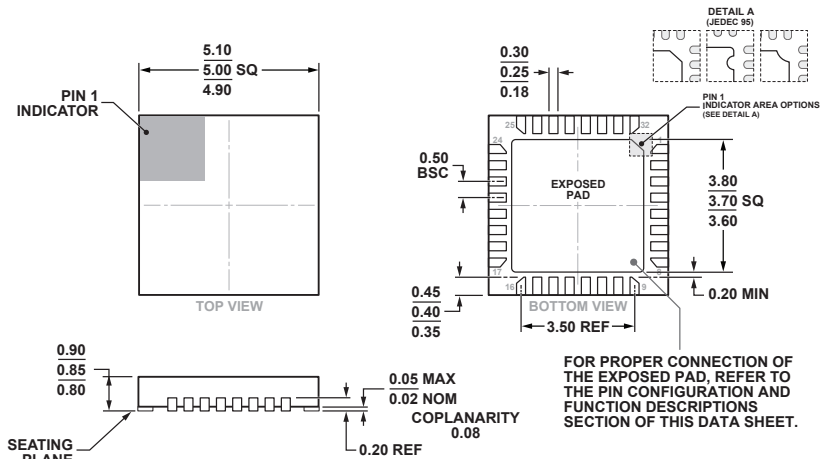
**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Absolute Maximum Ratings

Drain Bias Voltage (V _{dd})	+9V
Gate Bias Voltage (V _{gg1})	-2 to 0V
Gate Bias Current (I _{gg1})	2.5 mA
Gate Bias Voltage (V _{gg2})(AGC)	(V _{dd} -9) V _{dc} to +2V
RF Input Power (RFIN)(V _{dd} = +5V)	+18 dBm
Channel Temperature	150 °C
Continuous P _{diss} (T= 85 °C) (derate 19.1 mW/°C above 85 °C)	1.24 W
Thermal Resistance (channel to ground paddle)	52.3 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 0B - Passed 150V

Typical Supply Current vs. V_{dd}

V _{dd} (V)	I _{dd} (mA)
+4.5	58
+5.0	60
+5.5	62

**GaAs pHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**
7
Outline Drawing


COMPLIANT TO JEDEC STANDARDS MO-220-VHHD-4.

32-Lead Lead Frame Chip Scale Package [LFCSP]
5 mm × 5 mm Body and 0.90 mm Package Height
(HCP-32-1)

Dimensions shown in millimeters

Package Information

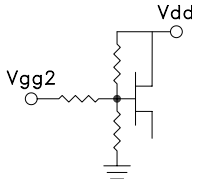
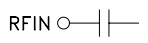
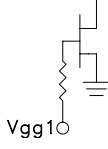
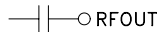
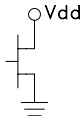

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC463LP5	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H463 XXXX
HMC463LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	H463 XXXX

[1] Max peak reflow temperature of 235 °C

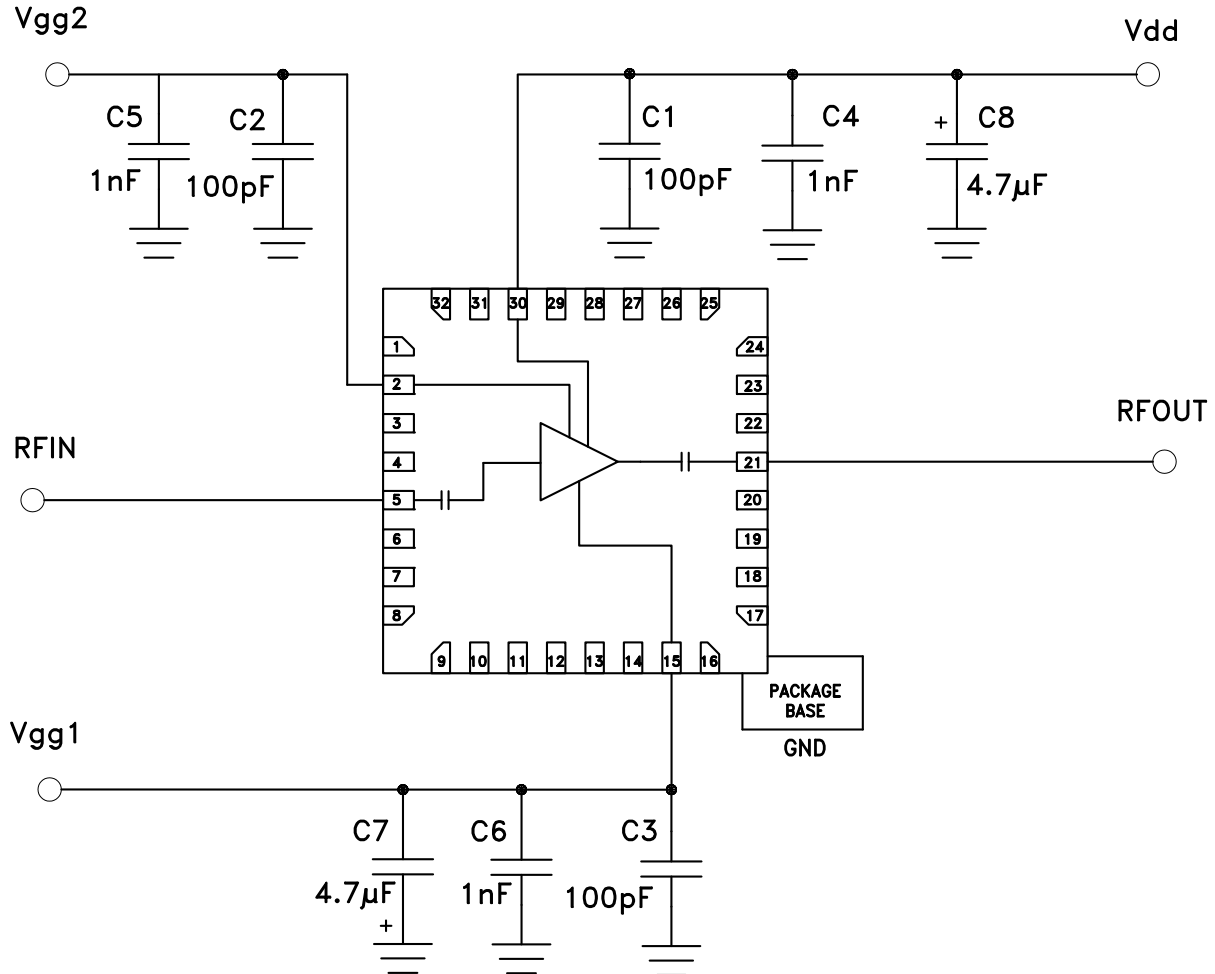
[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

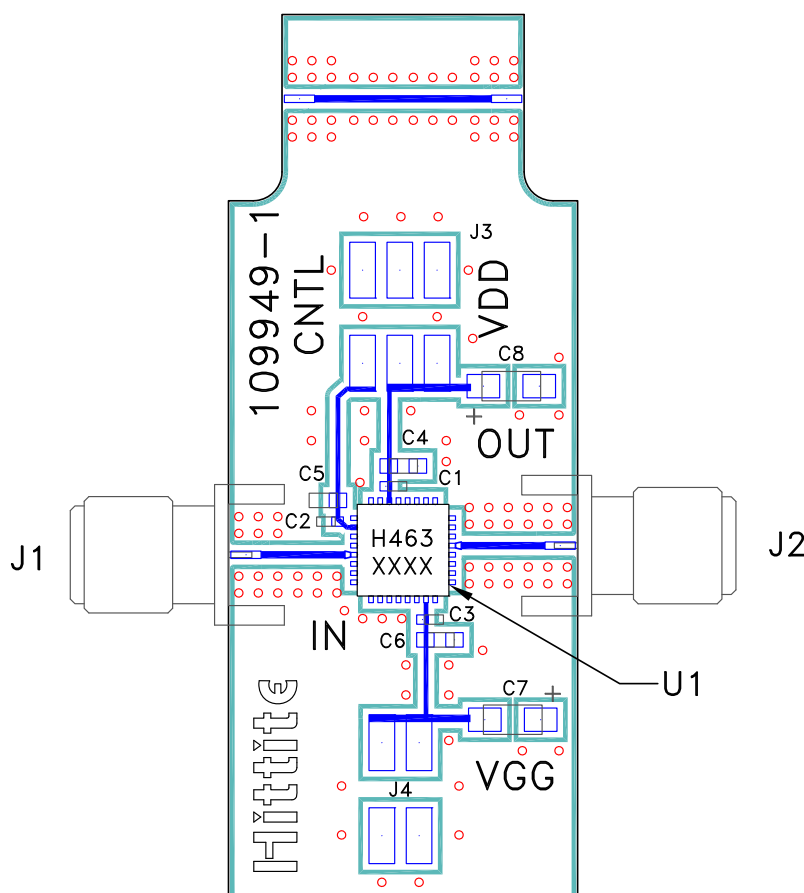
**GaAs pHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**
7
AMPLIFIERS - LOW NOISE - SMT
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 3, 4, 6-14, 16-20, 22-29, 31, 32	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
2	Vgg2	Optional gate control if AGC is required. Leave Vgg2 open circuited if AGC is not required. Typical Vgg2 = -1.5V to 0V	
5	RFIN	This pad is AC coupled and matched to 50 Ohms	
15	Vgg1	Gate control for amplifier. Adjust to achieve Idd = 60mA.	
21	RFOUT	This pad is AC coupled and matched to 50 Ohms	
30	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required	
Ground Paddle	GND	Ground paddle must be connected to RF/DC ground.	

Application Circuit



Evaluation PCB



List of Materials for Evaluation PCB 108341 ^[1]

Item	Description
J1 - J2	SRI K Connector
J3 - J4	2 mm Molex Header
C1 - C3	100 pF Capacitor, 0402 Pkg.
C4 - C6	1000 pF Capacitor, 0603 Pkg.
C7 - C8	4.7 μ F Capacitor, Tantalum
U1	HMC463LP5(E) Amplifier
PCB ^[2]	109949 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.